

Silicon NPN Power Transistors

2SC3352

DESCRIPTION

- With TO-220Fa package
- High voltage
- High speed switching

APPLICATIONS

- For high speed switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

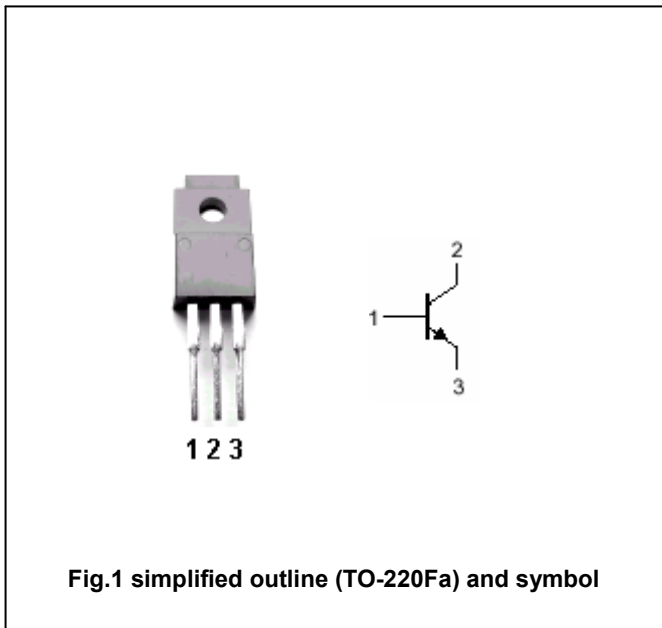


Fig.1 simplified outline (TO-220Fa) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	800	V
V _{CEO}	Collector-emitter voltage	Open base	500	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current		1.5	A
I _{CM}	Collector current-Peak		3.0	A
I _B	Base current		0.5	A
P _C	Collector power dissipation	T _C =25°C	25	W
		T _a =25°C	2	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA, I _B =0	500			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =1A; I _B =0.2A			1.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =1A; I _B =0.2A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE-1}	DC current gain	I _C =0.1A; V _{CE} =5V	15			
h _{FE-2}	DC current gain	I _C =1A; V _{CE} =5V	8			
f _T	Transition frequency	I _C =0.2A; V _{CE} =10V		2.5		MHz

Switching times

t _{on}	Turn-on time	I _C =1A; I _{B1} =-I _{B2} =0.2A V _{CC} =200V			1.0	μs
t _{stg}	Storage time				3.0	μs
t _f	Fall time				1.0	μs

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PACKAGE OUTLINE

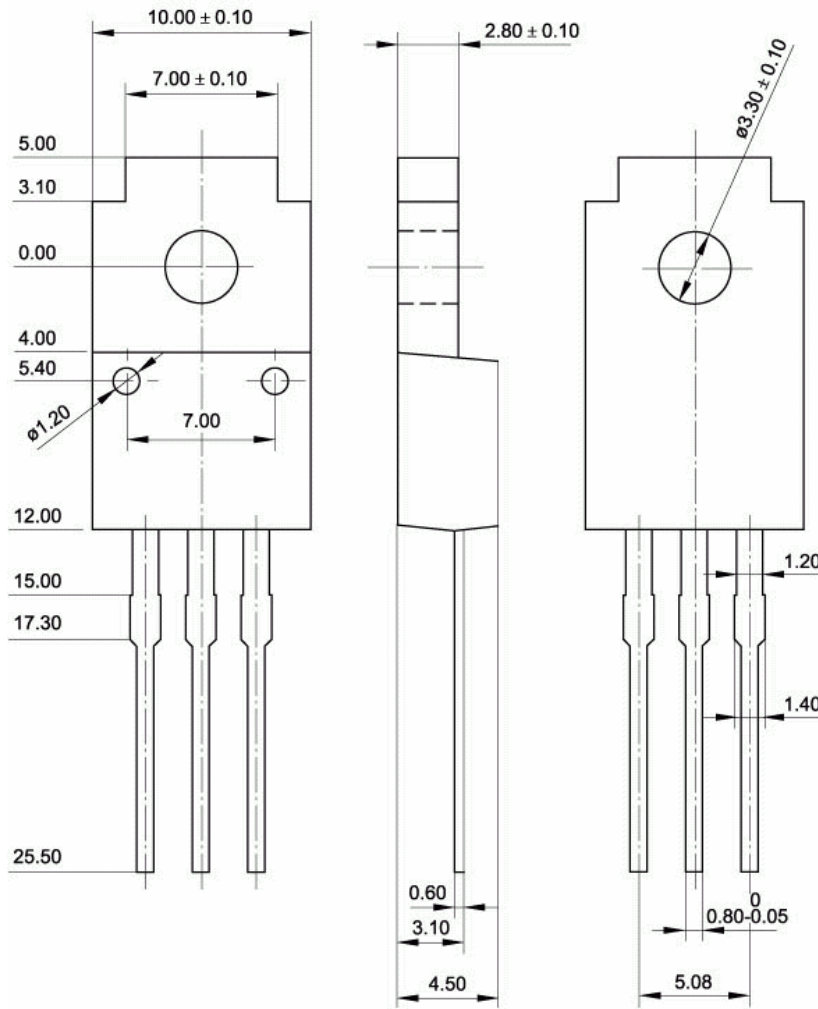


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)